#### SILICON (Si) POWER MOSFET A CEZC16R10LA



# CEZC16R10LA

# 100V ▲ 13.4mΩ ▲ 29A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy PPAK3x3 package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability

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**MAXIMUM RATINGS** 

Parameter ( $T_c = 25^{\circ}C$ , unless otherwise noted)	Characteristics	
Drain-Source Voltage	V <sub>DS</sub>	100V
Gate-Source Voltage	V <sub>GS</sub>	±20V
Continuous Drain Current at R <sub>TH_JC</sub>	I <sub>D</sub>	29A
Continuous Drain Current at R <sub>TH_JA</sub>	I <sub>D</sub>	9A
Pulsed Drain Current at R <sub>TH_JC</sub> Note 1	I <sub>DM</sub>	116A
Pulsed Drain Current at R <sub>TH_JA</sub> Note 1	I <sub>DM</sub>	36A
Maximum Power Dissipation	PD	25W
Single Pulsed Avalanche Energy Note 5	E <sub>AS</sub>	10mJ
Single Pulsed Avalanche Current Note 5	I <sub>AS</sub>	4.5A
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

#### THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R <sub>TH_JC</sub>	5°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>th_ja</sub>	50°C/W

#### **APPLICATIONS**

Battery Management Systems	E-Bike	Industrial Control	Power Inverter	UPS
+ 4 -	50			

## **PIN DESCRIPTION**

Circuit Diagram	Outline - Bottom View	Pin No.	Description
D (5) G (4) S (1,2,3)		1 2 3 4 5	Source Source Gate Drain

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HALOGEN

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#### **ELECTRICAL CHARACTERISTICS** A T<sub>c</sub> = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250 \mu A$	BV <sub>DSS</sub>	100			V
Zero Gate Voltage Drain Current	$V_{DS}$ = 100V, $V_{GS}$ = 0V	I <sub>DSS</sub>			10	μA
Gate Body Leakage Current, Forward	$V_{GS}$ = 20V, $V_{DS}$ = 0V	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS}$ = -20V, $V_{DS}$ = 0V	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu A$	$V_{GS(th)}$	1		2.5	V
Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 12A	R <sub>DS(ON)</sub>		13.4	16	mΩ
Static Drain-Source On-Resistance	$V_{GS}$ = 4.5V, $I_{D}$ = 7A	R <sub>DS(ON)</sub>		18.4	24	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS}$ = 50V, $V_{GS}$ = 0V, f = 1MHz	C <sub>ISS</sub>		900		pF
Output Capacitance	$V_{DS}$ = 50V, $V_{GS}$ = 0V, f = 1MHz	Coss		205		pF
Reverse Transfer Capacitance	$V_{DS}$ = 50V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		15		pF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{\text{DD}}$ = 50V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1A, $R_{\text{G}(\text{ext})}$ = 6 $\Omega$	t <sub>D(ON)</sub>		17		ns
Turn-On Rise Time	$V_{\text{DD}}$ = 50V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1A, $R_{G(\text{ext})}$ = 6 $\Omega$	t <sub>R</sub>		4		ns
Turn-Off Delay Time	$V_{\text{DD}}$ = 50V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1A, $R_{G(\text{ext})}$ = 6 $\Omega$	t <sub>D(OFF)</sub>		42		ns
Turn-Off Fall Time	$V_{\text{DD}}$ = 50V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1A, $R_{\text{G(ext)}}$ = 6 $\Omega$	t <sub>F</sub>		20		ns
Total Gate Charge	$V_{DS}$ = 50V, $V_{GS}$ = 4.5V, $I_{D}$ = 20A	Q <sub>G</sub>		11.5		nC
Gate Source Charge	$V_{DS}$ = 50V, $V_{GS}$ = 4.5V, $I_{D}$ = 20A	Q <sub>GS</sub>		1.7		nC
Gate Drain Charge	$V_{DS}$ = 50V, $V_{GS}$ = 4.5V, $I_{D}$ = 20A	$\mathbf{Q}_{GD}$		7.8		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current <sup>Note 2</sup>		١ <sub>s</sub>			20	А
Drain-Source Diode Forward Voltage Note 3	V <sub>GS</sub> = 0V, I <sub>S</sub> = 12A	$V_{\text{SD}}$			1.2	V

#### Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board,  $t \le 10$  sec.

3: Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4: Guaranteed by design, not subject to production testing.

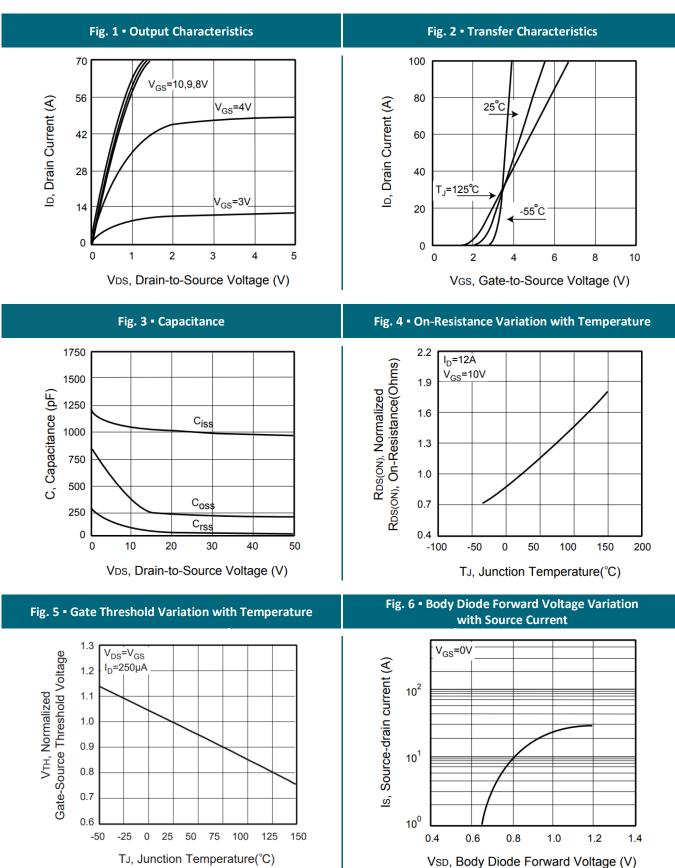
5: L = 1mH,  $I_{AS} = 4.5A$ ,  $V_{DD} = 24V$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}C$ 



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# **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**

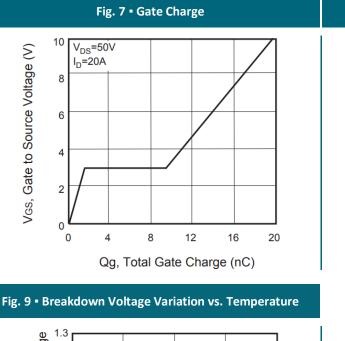


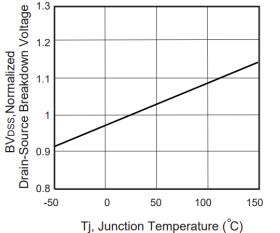
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## **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**





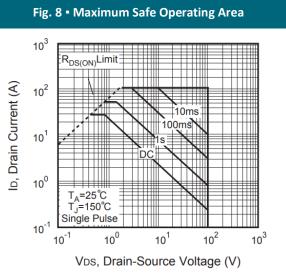


Fig. 10 • Switching Test Circuit Fig. 11 - Switching Waveforms VDD ton • toff tr td(off) RL td(on) tf VIN 90% 90% Vout D Vout INVERTED 10% 10% Vgs Rgen G K 90% 50% 50% Vin 10% S PULSE WIDTH

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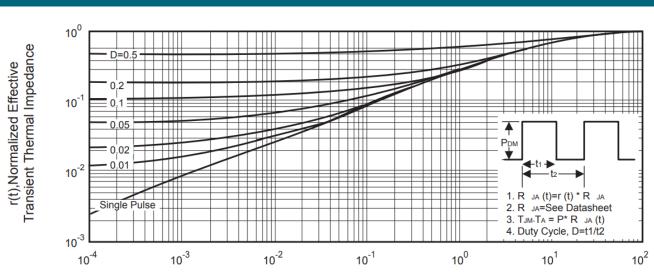
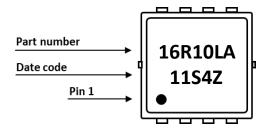


Fig. 12 • Normalized Thermal Transient Impedance Curve

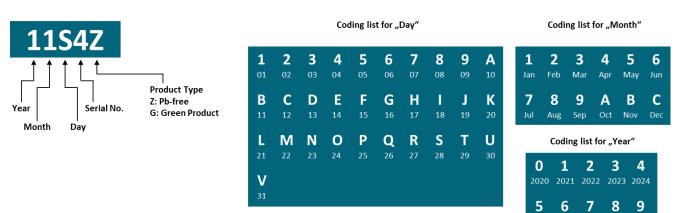
Square Wave Pulse Duration (sec)

#### **PART MARKING**



## DATE CODE

Example: 11S4Z



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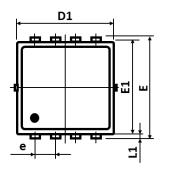
2025 2026 2027 2028 2029

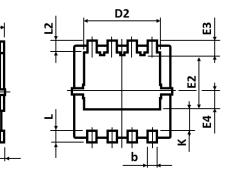
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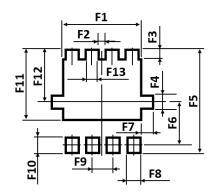


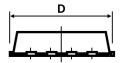
# PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT

С









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	0.700	-	0.850	E2	1.540	-	1.940
b	0.200	-	0.400	E3	0.280	-	0.650
с	0.100	-	0.250	E4	0.370	-	0.770
D	3.000	-	3.450	е		0.650 (BSC)	
D1	3.000	-	3.250	К	0.500	-	0.890
D2	2.290	-	2.650	L	0.300	-	0.500
E	3.150	-	3.450	L1	0.060	-	0.200
E1	2.900	-	3.200	L2	0.270	-	0.570

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	2.500	-	F8	-	0.350	-
F2	-	0.300	-	F9	-	0.650	-
F3	-	0.400	-	F10	-	0.500	-
F4	-	0.430	-	F11	-	2.280	-
F5	-	3.350	-	F12	-	1.700	-
F6	-	1.400	-	F13	-	0.350	-
F7	_	0.420	_				

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

## **ORDERING INFORMATION**

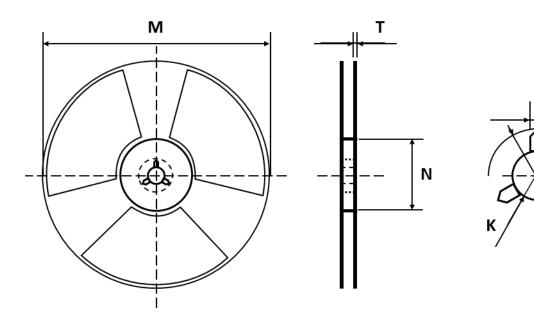
Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEZC16R10LA	PPAK 3x3	Reel	5,000pcs	10,000pcs	80,000pcs



S

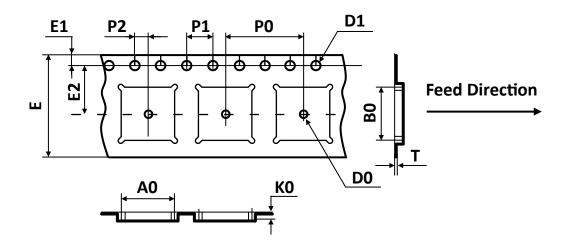
Н

#### **REEL DIMENSIONS** All dimensions in mm



Tape Size	Reel Size	М	N	Т	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
12mm	Ø330	±2.00	±1.00	±0.20	±0.50	+0.50 -0.20	±0.50

# TAPE DIMENSIONS All dimensions in mm



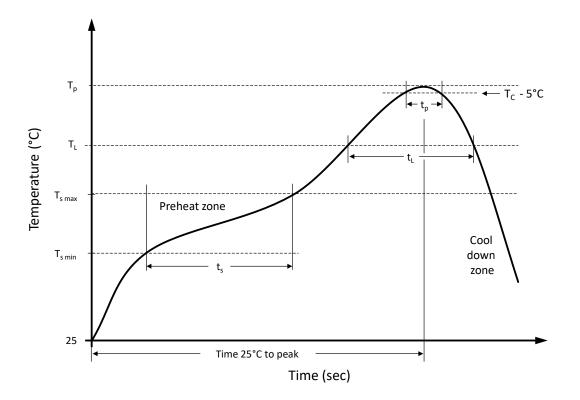
Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
	6.50	5.28	2.00	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
РРАК ЗхЗ	±0.10	±0.10	±0.10	±0.25	±0.10	+0.30 -0.10	±0.10	±0.05	±0.10	±0.10	±0.05	±0.02







#### **RECOMMENDED REFLOW SOLDERING PROFILE**



#### **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes

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#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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